IN THE ABSTRACT

Please replace the paragraph at page 23, line 2, with the following:

C3

A circuit device that includes a first transistor having a first metal gate electrode overlying a first gate dielectric on a first area of a semiconductor substrate. The first gate electrode has a work function corresponding to the work function of one of the P-type silicon and N-type silicon. The circuit device also includes a second transistor coupled to the first transistor. The second transistor has a second metal gate electrode over a second gate dielectric on a second area of the semiconductor substrate. The second gate metal gate electrode has a work function corresponding to the work function of the other one of P-type silicon and N-type silicon.

IN THE CLAIMS

Please substitute the following amended claims for the pending claims with the same numbers:

C4

Sub D1

1. (Amended) A circuit device comprising:

a first transistor including a first metal gate electrode over a first gate dielectric on a first area of a semiconductor substrate and having a work function corresponding to the work function of one of P-type silicon and N-type silicon;

a second transistor complementary to the first transistor including a second metal gate electrode over a second gate dielectric on a second different area of a semiconductor substrate and having a work function corresponding to the work function of the other one of P-type silicon and N-type silicon; and

wherein the first metal gate electrode and the second metal gate electrode are separately disposed in respective ones of the first area and the second area of the semiconductor substrate.

C4 end Sub H1

2. (Amended) The circuit device of claim 1, wherein the first metal gate electrode is one of a pure metal, a doped metal, and a metal alloy.

Please add the following new claims:

C5 Sub H1

16. (New) The circuit device of claim 1, wherein the first gate dielectric is silicon dioxide.

17. (New) The circuit device of claim 1, wherein the first metal gate electrode is one of tantalum, tantalum nitride, molybdenum silicide, and molybdenum nitride.

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